

Rev. 2.9

# 32K X 8 BIT LOW POWER CMOS SRAM

# **REVISION HISTORY**

Revision	<u>Description</u>	Issue Date
Rev. 1.0.	Initial Issue	Jul.25.2004
Rev. 2.0.	Revised Vcc Range(Vcc=4.5~5.5V => 2.7~5.5V)	May.4.2005
Rev. 2.1.	Revised I <sub>SB1</sub>	May.13.2005
Rev. 2.2	Adding PKG type : skinny P-DIP	Aug.29.2005
Rev. 2.3	Revised V <sub>IH</sub> (min)=2.4V, V <sub>IL</sub> (max)=0.6V	Feb.24.2006
Rev. 2.4	Revised V <sub>IH</sub> (min)=2.4V, V <sub>IL</sub> (max)=0.6V (V <sub>CC</sub> =2.7~3.6V)	Jul.31.2006
	V <sub>IH</sub> (min)=2.4V, V <sub>IL</sub> (max)=0.8V (V <sub>CC</sub> =4.5~5.5V)	
Rev. 2.5	Revised STSOP Package Outline Dimension	Mar.26.2008
Rev. 2.6	Added SL grade	Mar.30.2009
	Added $I_{SB1}/I_{DR}$ values when $T_A = 25^{\circ}C$ and $T_A = 40^{\circ}C$	
	Revised <b>FEATURES</b> & <b>ORDERING INFORMATION Lead</b>	
	free and green package available to Green package available	
	Added packing type in <b>ORDERING INFORMATION</b>	
	Revised I <sub>SB1(MAX)</sub>	
	Revised VTERM to VT1 and VT2	
	Revised Test Condition of Isb1/IDR	
	Deleted Tsolder in ABSOLUTE MAXIMUN RATINGS	
Rev. 2.7	Revised <b>PACKAGE OUTLINE DIMENSION</b> in page 8 & 9	Dec.18.2009
Rev. 2.8	Revised PACKAGE OUTLINE DIMENSION in page 10	May.7.2010
Rev. 2.9	Revised <b>ORDERING INFORMATION</b> in page 12	Aug.25.2010
	Revised PACKAGE OUTLINE DIMENSION in page 9	

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# **FEATURES**

■ Fast access time : 35/55/70ns■ Low power consumption:

Operating current : 20/15/10mA (TYP.)

Standby current : 1µA (TYP.)
■ Single 2.7~5.5V power supply

■ All inputs and outputs TTL compatible

■ Fully static operation

■ Tri-state output

■ Data retention voltage : 1.5V (MIN.)

■ Green package available

■ Package: 28-pin 600 mil PDIP

28-pin 330 mil SOP

28-pin 8mm x 13.4mm STSOP 28-pin 300 mil Skinny P-DIP

### **GENERAL DESCRIPTION**

The LY62256 is a 262,144-bit low power CMOS static random access memory organized as 32,768 words by 8 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

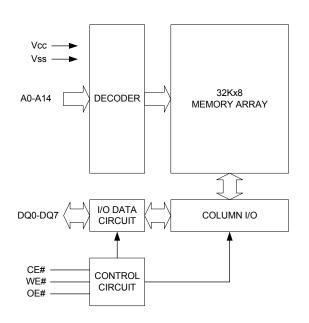
The LY62256 is well designed for low power application, and particularly well suited for battery back-up nonvolatile memory application.

The LY62256 operates from a single power supply of 2.7~5.5V and all inputs and outputs are fully TTL compatible

### PRODUCT FAMILY

Product	Operating	Vec Pange	Speed	Power D	issipation
Family	Temperature	Vcc Range	Speed	Standby(IsB1,TYP.)	Operating(Icc,TYP.)
LY62256	0 ~ 70℃	2.7 ~ 5.5V	35/55/70ns	1µA	20/15/10mA
LY62256(E)	-20 ~ 80℃	2.7 ~ 5.5V	35/55/70ns	1µA	20/15/10mA
LY62256(I)	-40 ~ 85°C	2.7 ~ 5.5V	35/55/70ns	1µA	20/15/10mA

## **FUNCTIONAL BLOCK DIAGRAM**



## **PIN DESCRIPTION**

SYMBOL	DESCRIPTION
A0 - A14	Address Inputs
DQ0 – DQ7	Data Inputs/Outputs
CE#	Chip Enable Input
WE#	Write Enable Input
OE#	Output Enable Input
Vcc	Power Supply
Vss	Ground

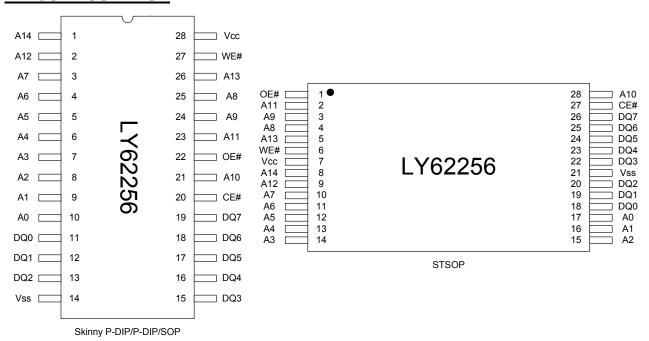
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### **PIN CONFIGURATION**



# **ABSOLUTE MAXIMUN RATINGS\***

PARAMETER	SYMBOL	RATING	UNIT
Voltage on Vcc relative to Vss	VT1	-0.5 to 6.5	V
Voltage on any other pin relative to Vss	VT2	-0.5 to Vcc+0.5	V
		0 to 70(C grade)	
Operating Temperature	TA	-20 to 80(E grade)	$^{\circ}\!\mathbb{C}$
		-40 to 85(I grade)	
Storage Temperature	Тѕтс	-65 to 150	$^{\circ}$
Power Dissipation	PD	1	W
DC Output Current	Іоит	50	mA

<sup>\*</sup>Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

### **TRUTH TABLE**

MODE	CE#	OE#	WE#	I/O OPERATION	SUPPLY CURRENT
Standby	Н	X	Х	High-Z	ISB,ISB1
Output Disable	L	Н	Н	High-Z	Icc,Icc1
Read	L	L	Н	Dout	Icc,Icc1
Write	L	Х	L	Din	Icc,Icc1

Note:  $H = V_{IH}$ ,  $L = V_{IL}$ , X = Don't care.

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## **DC ELECTRICAL CHARACTERISTICS**

PARAMETER	SYMBOL	TEST CONDITI	ON	MIN.	TYP. <sup>^4</sup>	MAX.	UNIT
Supply Voltage	Vcc			2.7	3.3	5.5	V
Input High Voltage	V <sub>IH</sub> <sup>*1</sup>			2.4	-	Vcc+0.5	V
Input Low Voltage	V <sub>IL</sub> *2	Vcc=2.7~3.6V		- 0.5	-	0.6	V
Input Low Voltage	V IL	Vcc=4.5~5.5V		- 0.5	-	0.8	V
Input Leakage Current	ILI	$Vcc \ge Vin \ge Vss$		- 1	-	1	μA
Output Leakage Current	ILO	$V_{CC} \ge V_{OUT} \ge V_{SS}$ , Output Disabled		- 1	-	1	μA
Output High Voltage	Vон	Iон = -1mA		2.4	3.0	-	V
Output Low Voltage	Vol	I <sub>OL</sub> = 2mA		-	-	0.4	V
	Icc	Cycle time = Min.	-35	-	20	50	mΑ
		CE# = V <sub>IL</sub> , I <sub>I/O</sub> = 0mA	-55	-	15	45	mA
Average Operating		Other pins at V <sub>IL</sub> or V <sub>IH</sub>	-70	-	10	40	mA
Power supply Current	lcc <sub>1</sub>	Cycle time = $1\mu$ s CE# $\leq$ 0.2V and $I_{VO}$ = 0r other pins at 0.2V or Vo	-	3	10	mA	
	IsB	CE# = V <sub>IH</sub> , other pins at	VIL or VIH	-	1	3	mΑ
			LL	-	1	20	μA
			LLE/LLI	-	1	30	μΑ
Standby Power	I <sub>SB1</sub>	CE# ≧Vcc-0.2V Others at 0.2V or	SL <sup>*5</sup> 25℃	-	1	3	μA
Supply Current	ISB1	Vcc - 0.2V	SLI <sup>™</sup> 40°C	-	1.5	4	μA
			SL	-	1	10	μA
Notoo		ļ	SLE/SLI	-	1	20	μA

### Notes:

- 1. VIH(max) = Vcc + 3.0V for pulse width less than 10ns.
- 2. V<sub>IL</sub>(min) = V<sub>SS</sub> 3.0V for pulse width less than 10ns.
- 3. Over/Undershoot specifications are characterized, not 100% tested.
- 4. Typical values are included for reference only and are not guaranteed or tested. Typical valued are measured at  $V_{CC}$  =  $V_{CC}$ (TYP.) and  $T_A$  = 25 $^{\circ}$ C
- 5. This parameter is measured at Vcc = 3.0V

## **CAPACITANCE** (TA = $25^{\circ}$ C, f = 1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	Cin	-	6	pF
Input/Output Capacitance	Ci/O	-	8	pF

Note: These parameters are guaranteed by device characterization, but not production tested.

## **AC TEST CONDITIONS**

Input Pulse Levels	0.2V to V <sub>CC</sub> - 0.2V
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 50pF + 1TTL$ , $I_{OH}/I_{OL} = -1mA/2mA$

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# **AC ELECTRICAL CHARACTERISTICS**

### (1) READ CYCLE

PARAMETER	SYM.	LY62256-35		LY62256-55		LY62256-70		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	<b>t</b> RC	35	-	55	-	70	-	ns
Address Access Time	<b>t</b> AA	-	35	-	55	-	70	ns
Chip Enable Access Time	<b>t</b> ACE	-	35	-	55	-	70	ns
Output Enable Access Time	toe	-	25	-	30	-	35	ns
Chip Enable to Output in Low-Z	tcLz*	10	-	10	-	10	-	ns
Output Enable to Output in Low-Z	tolz*	5	-	5	-	5	-	ns
Chip Disable to Output in High-Z	tcHz*	-	15	-	20	-	25	ns
Output Disable to Output in High-Z	tonz*	-	15	-	20	-	25	ns
Output Hold from Address Change	tон	10	-	10	-	10	-	ns

### (2) WRITE CYCLE

PARAMETER	SYM.	SYM. LY62256-35		LY62256-55		LY62256-70		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	twc	35	-	55	-	70	-	ns
Address Valid to End of Write	taw	30	-	50	-	60	-	ns
Chip Enable to End of Write	tcw	30	-	50	-	60	-	ns
Address Set-up Time	tas	0	-	0	-	0	-	ns
Write Pulse Width	twp	25	-	45	-	55	-	ns
Write Recovery Time	twr	0	-	0	-	0	-	ns
Data to Write Time Overlap	tow	20	-	25	-	30	-	ns
Data Hold from End of Write Time	<b>t</b> DH	0	-	0	-	0	-	ns
Output Active from End of Write	tow*	5	-	5	-	5	-	ns
Write to Output in High-Z	twnz*	-	15	-	20	-	25	ns

<sup>\*</sup>These parameters are guaranteed by device characterization, but not production tested.

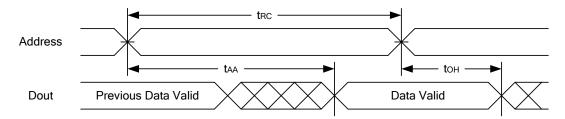


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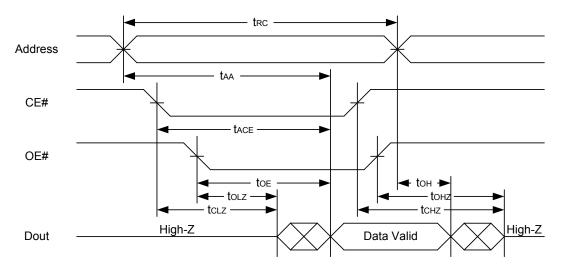
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# **TIMING WAVEFORMS**

### READ CYCLE 1 (Address Controlled) (1,2)



#### READ CYCLE 2 (CE# and OE# Controlled) (1,3,4,5)



#### Notes:

- 1.WE# is high for read cycle.
- 2.Device is continuously selected OE# = low, CE# = low.
- 3.Address must be valid prior to or coincident with CE# = low,; otherwise tAA is the limiting parameter.
- 4.tclz, tolz, tchz and tohz are specified with Cl = 5pF. Transition is measured  $\pm 500mV$  from steady state.
- 5.At any given temperature and voltage condition,  $t_{CHZ}$  is less than  $t_{CLZ}$ ,  $t_{OHZ}$  is less than  $t_{OLZ}$ .

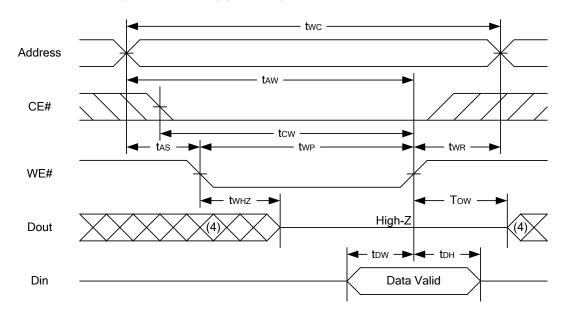
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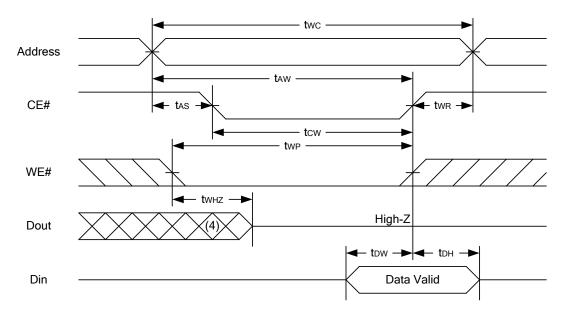
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#### WRITE CYCLE 1 (WE# Controlled) (1,2,3,5,6)



### WRITE CYCLE 2 (CE# Controlled) (1,2,5,6)



#### Notes

- 1.WE#, CE# must be high during all address transitions.
- 2.A write occurs during the overlap of a low CE#, low WE#.
- 3.During a WE# controlled write cycle with OE# low, twp must be greater than twHz + tpw to allow the drivers to turn off and data to be placed on the bus.
- 4. During this period, I/O pins are in the output state, and input signals must not be applied.
- 5.If the CE# low transition occurs simultaneously with or after WE# low transition, the outputs remain in a high impedance state.
- 6.tow and  $\text{tw}_{\text{HZ}}$  are specified with  $\text{C}_{\text{L}}$  = 5pF. Transition is measured  $\pm 500\text{mV}$  from steady state.



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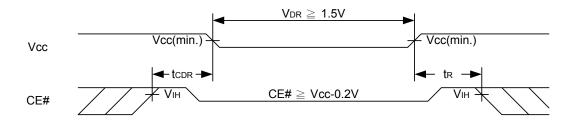
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# **DATA RETENTION CHARACTERISTICS**

PARAMETER	SYMBOL	TEST CONDITION	N		MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention	VDR	$CE\# \ge V_{CC} - 0.2V$			1.5	-	5.5	V
			LL/LLE/LLI		-	0.5	20	μΑ
Data Retention Current		V <sub>CC</sub> = 1.5V	SL SLE	<b>25</b> ℃	-	0.5	2	μA
	IDR	CE# $\geq$ Vcc - 0.2V Others at 0.2V or Vcc-0.2V		40°C	-	1	3	μΑ
			SL		1	0.5	8	μΑ
			SLE/SLI		1	0.5	15	μΑ
Chip Disable to Data Retention Time	†CDD	See Data Retention Waveforms (below)		0	-	-	ns	
Recovery Time	<b>t</b> R				<b>t</b> RC∗	ı	-	ns

tRC∗ = Read Cycle Time

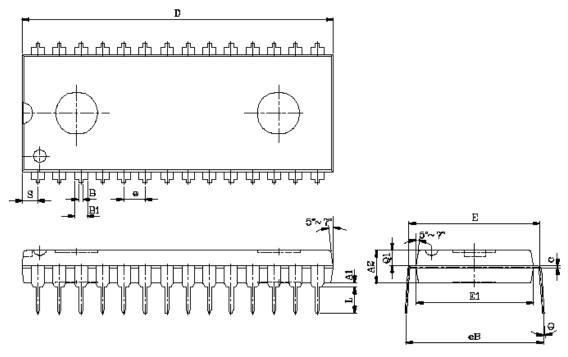
# **DATA RETENTION WAVEFORM**





# **PACKAGE OUTLINE DIMENSION**

### 28 pin 600 mil PDIP Package Outline Dimension

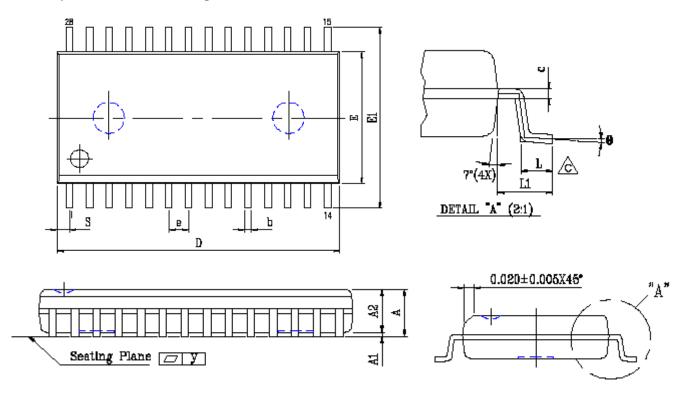


UNIT SYM.	INCH.(BASE)	MM(REF)
A1	0.015(MIN)	0.381(MIN)
A2	0.155±0.005	3.937±0.127
В	0.020(MAX)	0.508(MAX)
B1	0.060(TYP)	1.524(TYP)
С	0.012(MAX)	0.304(MAX)
D	1.470(MAX)	37.338(MAX)
Е	0.6(TYP)	15.24(TYP)
E1	0.55(MAX)	13.970(MAX)
е	0.100(TYP)	2.540(TYP)
eB	0.650±0.020	16.510±0.508
L	0.200(MAX)	5.080(MAX)
S	0.06(MAX)	1.524(MAX)
Q1	0.08(MAX)	2.032(MAX)
Θ	15°(MAX)	15°(MAX)



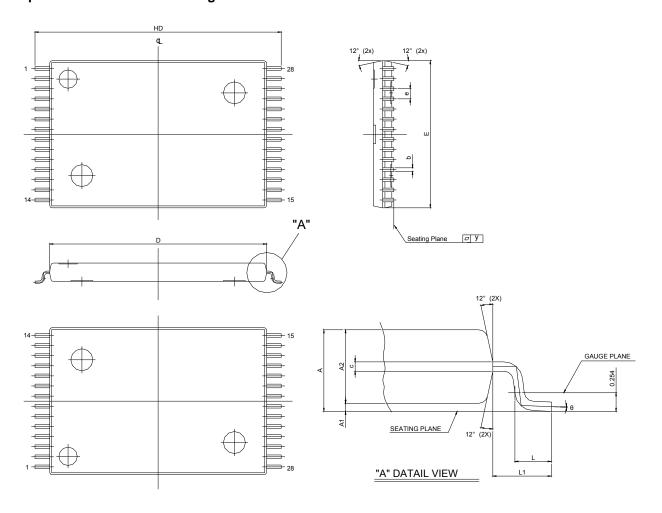


## 28 pin 330 mil SOP Package Outline Dimension



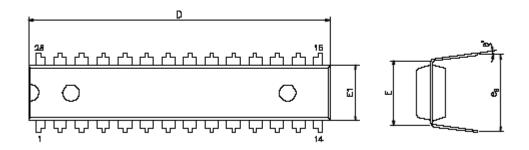
SYM. UNIT	INCH(BASE)	MM(REF)
Α	0.120(MAX)	3.048(MAX)
A1	0.002(MIN)	0.05(MIN)
A2	0.098±0.005	2.489±0.127
b	0.016(TYP)	0.406(TYP)
С	0.010(TYP)	0.254(TYP)
D	0.728(MAX)	18.491(MAX)
E	0.340(MAX)	8.636(MAX)
E1	0.465±0.012	11.811±0.305
е	0.050(TYP)	1.270(TYP)
L	0.038(MAX)	0.965(MAX)
L1	0.067±0.008	1.702 ±0.203
S	0.047(MAX)	1.194(MAX)
у	0.004(MAX)	0.102(MAX)
Θ	0°~10°	0°~10°

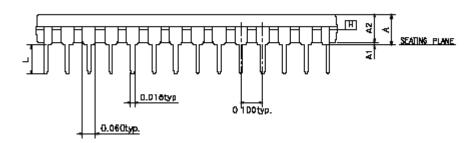
## 28 pin 8x13.4mm STSOP Package Outline Dimension



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
STIVIBULS	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.00	1.10	1.20	0.040	0.043	0.047
A1	0.05	-	0.15	0.002	-	0.006
A2	0.91	1.00	1.05	0.036	0.039	0.041
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.07	0.15	0.23	0.003	0.006	0.009
HD	13.20	13.40	13.60	0.520	0.528	0.535
D	11.60	11.80	12.00	0.457	0.465	0.472
Е	7.80	8.00	8.20	0.307	0.315	0.323
е	-	0.55	-	-	0.0216	-
L	0.30	0.50	0.70	0.012	0.020	0.028
L1	0.675	-	-	0.027	-	-
Y	0.00	-	0.076	0.000	-	0.003
θ	0°	3°	5°	0°	3°	5°

## 28 pin 300 mil PDIP Package Outline Dimension





SYMBOLS	MIN.	NOR.	MAX.	
Α	ı	1	0.210	
A1	0.015	ı	_	
A2	0.125	0.130	0.135	
D	1.385	1.390	1.400	
E	0.310 BSC			
E1	0.283	0.288	0.293	
L	0.115	0.130	0.150	
₽ <sub>B</sub>	0.330	0.350	0.370	
а	0	7	15	

UNIT: INCH

NOTE:

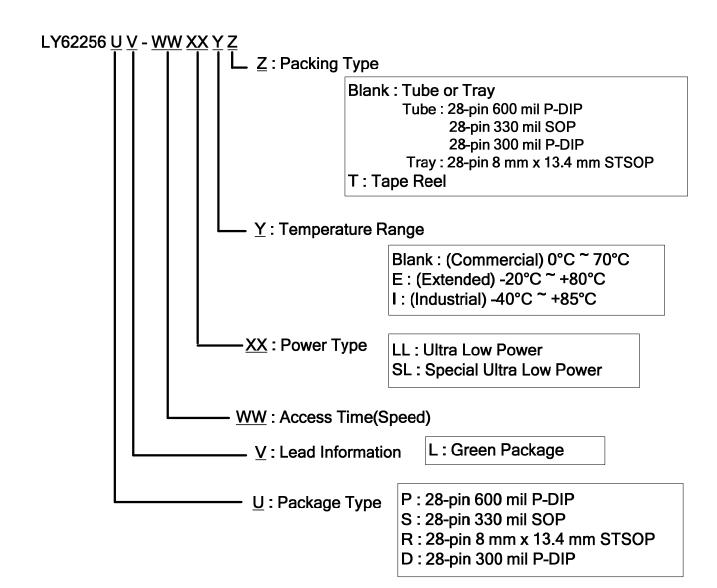
1.JEDEC OUTLINE : MS-D15 AH





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### **ORDERING INFORMATION**





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